



MMIC SURFACE MOUNT

SP4T RF Switch

HSWA4-63DR+

Absorptive RF Switch with Internal Driver
Single Supply Voltage, +2.3 V to +5.5 V

THE BIG DEAL

- High Isolation, 61 dB at 0.9 GHz
- Low Insertion Loss, 0.9 dB at 0.9 GHz
- High IP3, +58 dBm
- Fast Switching, 255 ns Typ.
- Low Current Consumption, 110 μ A
- Immune to Latch-Up

APPLICATIONS

- Defense
- Test and Measurements
- Switch Matrices

PRODUCT OVERVIEW

Mini-Circuits' HSWA4-63DR+ is a MMIC SP4T absorptive switch with an internal driver designed for wideband operation from 30 MHz to 6000 MHz, supporting many applications requiring high performance across a wide frequency range. This model provides excellent isolation, fast switching speed and high linearity in a tiny 4x4 mm 24-Lead MCLP package. Produced using a unique CMOS process on silicon, it offers the performance of GaAs with the advantages of conventional CMOS devices. HSWA4-63DR+ provides a high level of ESD protection, MSL1 moisture sensitivity rating, and excellent repeatability.



CASE STYLE: DG984-1

Generic photo used for illustration purposes only

+RoHS Compliant

The +Suffix identifies RoHS Compliance.
See our website for methodologies and qualifications

KEY FEATURES

Feature	Advantages
Wideband, 30 MHz to 6000 MHz	One model can be used in many applications, saving component count. Also ideal for wideband applications such as military and instrumentation.
Absorptive Switch	In the off condition, RF output ports which are not switched ON are terminated into 50 Ω . This enables proper impedance termination of the circuitry following the RF output ports, preventing any unintended action such as oscillation.
High Isolation: <ul style="list-style-type: none"> • 61 dB at 0.9 GHz • 32 dB at 6 GHz 	High isolation significantly reduces leakage of power into OFF ports.
High Linearity <ul style="list-style-type: none"> • +58 dBm IIP3 • +97 dBm IIP2 at 1.9 GHz 	High linearity minimizes unwanted intermodulation products which are difficult or impossible to filter in multi-carrier environments such as CATV, or in the presence of strong interfering signal from adjacent circuitry or received by antenna.
Built-In Negative Voltage Generator	Operates with single positive supply voltage; no need for DC blocking capacitors, unless external DC is present at the RF ports.
Built-In CMOS Driver	No need for external driver, saving PCB space and cost.
Wide Supply Voltage and Low Current +2.3 to +5.5 V and 110 μ A Typ.	Ideal for battery operated systems consuming very low current for long battery life.
Immune to Latch-Up	Unlike conventional CMOS devices, HSWA is immune to latch-up
Tiny Size, 4x4 mm QFN Package	Tiny footprint saves space in dense layouts while providing low inductance, repeatable transitions, and excellent thermal contact to the PCB.



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RF ELECTRICAL SPECIFICATIONS¹, 30 MHz-6000 MHz, T_{AMB} = +25°C, V_{DD} = +3.3 V

Parameter	Condition (MHz)	Min.	Typ.	Max.	Units
Frequency Range		30		6000	MHz
Insertion Loss ²	30-900		0.9	1.1	dB
	900-2100		1.1	1.35	
	2100-2700		1.15	1.4	
	2700-4000		1.25	1.5	
	4000-6000		1.9	2.5	
Isolation Between Common Port and Output Ports	30-900	55	61		dB
	900-2100	52	55		
	2100-2700	50	52		
	2700-4000	42	43		
	4000-6000	27	32		
Isolation Among Output Ports	30-900	56	61		dB
	900-2100	51	54		
	2100-2700	50	52		
	2700-4000	41	44		
	4000-6000	29	32		
Return Loss (ON STATE)	30-4000		17		dB
	4000-6000		12		
Return Loss (OFF STATE)	30-4000		22		dB
	4000-6000		19		
Input IP2	1900		+97		dBm
Input IP3	1900		+58		dBm
0.1 dB Input Compression ³	900		+35		dBm
RF Input Operating Power, CW	30-6000			+33	dBm
RF Input Power Into Terminated Output Ports, CW	30-6000			+24	dBm

1. Tested on Mini-Circuits' test board TB-927+, using Agilent's N5230A network analyzer (see Characterization test circuit, Fig.1).

2. Insertion loss values are de-embedded from test board loss.

3. Do not exceed RF input power as shown in Absolute Maximum Ratings table.

DC ELECTRICAL SPECIFICATIONS

Parameter	Min.	Typ.	Max.	Units
Supply Voltage, V _{DD}	+2.3		+5.5	V
Supply Current		110		μA
Control Voltage Low	-0.3		+0.6	V
Control Voltage High	+1.17		+3.6	V
Control Current			1	μA

SWITCHING SPECIFICATIONS

Parameter	Condition	Min.	Typ.	Max.	Units
Switching Time 50% Control to 90/10% RF	f _{FR} = 50 MHz f _{ctrl} = 50 KHz V _{ctrl} High = +3.3 V V _{ctrl} Low = 0 V		255	330	nS
Video Feed-Through			14		mV _{p-p}
Rise/Fall Time 10 to 90% or 90 to 10%			100		nS



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ABSOLUTE MAXIMUM RATINGS⁴

Parameter	Ratings
Operating Temperature	-40°C to +105°C
Storage Temperature	-65°C to +150°C
V _{DD} , Supply Voltage	-0.3 to +5.5 V
Voltage Control	-0.3 V min. +3.6 V max.
RF Input Power, CW	+34 dBm

4. Operation of this device above any of these conditions may cause permanent damage.

TRUTH TABLE - 3 PIN CONTROL

Mode	State of Control Voltage		
	Control 3	Control 2	Control 1
RF COM - RF1 ON	LOW	LOW	HIGH
RF COM - RF2 ON	LOW	HIGH	LOW
RF COM - RF3 ON	LOW	HIGH	HIGH
RF COM - RF4 ON	HIGH	LOW	LOW
	LOW	LOW	LOW
ALL OFF	HIGH	LOW	HIGH
ALL OFF	HIGH	HIGH	LOW
Unsupported	HIGH	HIGH	HIGH

TRUTH TABLE - 2 PIN CONTROL⁵

Mode	State of Control Voltage	
	Control 2	Control 1
RF COM - RF1 ON	LOW	HIGH
RF COM - RF2 ON	HIGH	LOW
RF COM - RF3 ON	HIGH	HIGH
RF COM - RF4 ON	LOW	LOW

5. Pad 19 = control 3 must be grounded.



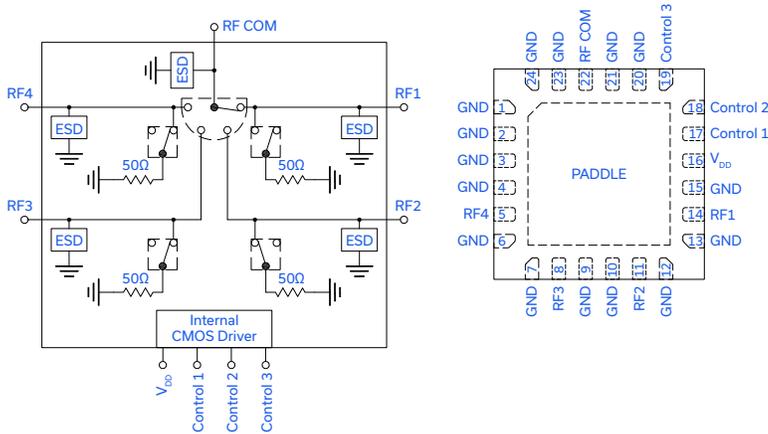
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SIMPLIFIED SCHEMATIC AND PAD DESCRIPTION



Function	Pad Number	Description
RF COM	22	RF Common/ SUM port*
RF1	14	RF out #1/In port #1*
RF2	11	RF out #2/In port #3*
RF3	8	RF out #3/In port #2*
RF4	5	RF out #4/In port #4*
Control 1	17	CMOS Control IN #1
Control 2	18	CMOS Control IN #2
Control 3	19	CMOS Control IN #3
V _{DD}	16	Supply voltage
GND	1-4,6,9,10,12,13,15, 20,21,23,24	RF Ground

* Must be held at 0 VDC. If required add DC blocking capacitors on these ports.

CHARACTERIZATION & APPLICATION CIRCUIT

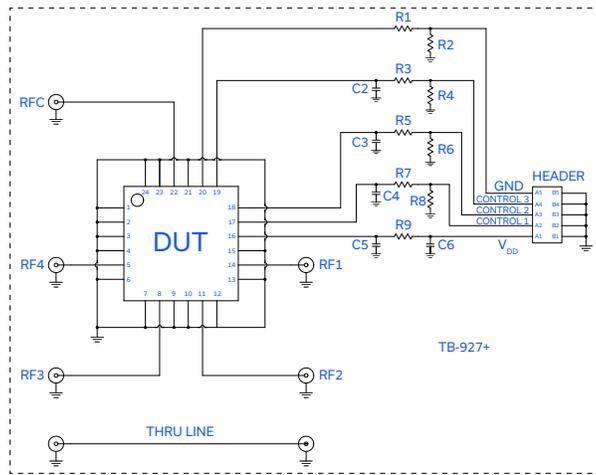


Figure 1. Block Diagram of test Circuit used for characterization (DUT soldered on Mini-Circuit's TB-927+)

Component	Value	Size
DUT	HSWA4-63DR+	4x4 mm
C2, C3, C4, C5	100 pF	0402
C6	1 uF	
R1, R2, R3, R5, R7, R9	0 Ohm	
R4, R6, R8	1 MOhm	

PRODUCT MARKING

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Marking may contain other features or characters for internal lot control.

Parameter	Conditions V _{DD} = +2.3 V and +5.5 V Control = 0 V and +3.3 V	Test Equipment
Insertion Loss, Isolation, Return Loss and DC Current	P _{IN} = 0 dBm	Keysight N5242A Network Analyzer, E3631A power supply. Cblock: Internal to network Analyzer.
Switching Time and DC Current	RF Frequency: 50 MHz at 0 dBm, Control Frequency: 50 KHz	Keysight 54832B oscilloscope, 81110A pulse generator and E3631A power supply
Input IP3	+15 dBm/Tone	Keysight ES257D signal generators, E4416A power meter, N9020A Signal analyzer and E3631A power supply
Compression		Keysight N5242A Network Analyzer, E3631A power supply





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ADDITIONAL DETAILED TECHNICAL INFORMATION IS AVAILABLE ON OUR DASHBOARD. TO ACCESS [CLICK HERE](#)

Performance Data	Data Table Swept Graphs
Case Style	DG984-1 Plastic package, exposed paddle, Termination Finish: NiPdAu
Tape & Reel Standard Quantities Available on Reel	F68 7" Reels with 20, 50, 100, 200, 500, 1000, or 3000 devices
Suggested Layout for PCB Design	PL-514
Evaluation Board	TB-927+
Environmental Ratings	ENV84

ESD RATING

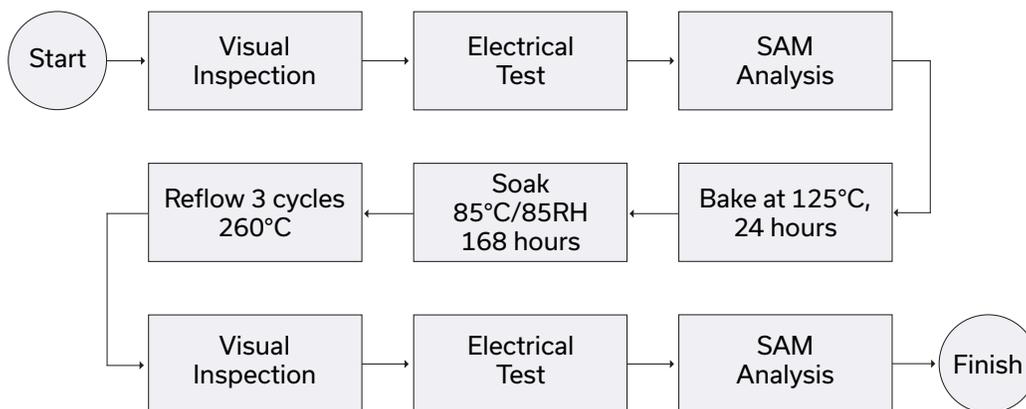
Human Body Model (HBM): Class 2 (Pass 2000 V) in accordance with MIL-STD-883, Method 3015

Charge Device Model (CDM): Class C1 (Pass 250 V) in accordance with JESD22-C101

MSL RATING

Moisture Sensitivity: MSL1 in accordance with IPC/JEDEC J-STD-020D

MSL TEST FLOW CHART



- NOTES**
- A. Performance and quality attributes and conditions not expressly stated in this specification document are intended to be excluded and do not form a part of this specification document.
 - B. Electrical specifications and performance data contained in this specification document are based on Mini-Circuit's applicable established test performance criteria and measurement instructions.
 - C. The parts covered by this specification document are subject to Mini-Circuits standard limited warranty and terms and conditions (collectively, "Standard Terms"); Purchasers of this part are entitled to the rights and benefits contained therein. For a full statement of the standard. Terms and the exclusive rights and remedies thereunder, please visit Mini-Circuits' website at www.minicircuits.com/terms/viewterm.html

